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Disorder effect on the localization/delocalization in incommensurate potential

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The interplay between incommensurate (IC) and random potentials is studied in a two-dimensional symplectic model with the focus on localization/delocalization problem. With the IC potential only, there appear wavefunctions localized along the IC wavevector while extended perpendicular to it. Once the disorder potential is introduced, these turn into two-dimensional anisotropic metallic states beyond the scale of the elastic mean free path, and eventually becomes localized in both directions at a critical strength of the disorder. Implications of these results to the experimental observation of the IC-induced localization is discussed.

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The localization/delocalization of the electronic wavefunctions is one of the most fundamental problems in condensed matter physics. In the presence of the disorder, the interference among the scattered waves leads to the quantum correction to the Boltzmann transport theory and eventually to the Anderson localization [1]. This is most prominent in one-dimension, where all the states are localized for any finite strength of the disorder potential. There is another type of localization, which is induced by the incommensurate (IC) potential as first discussed by Aubry-Andre[2, 3]. In this case, even in one-dimension, there is a critical strength of the IC potential at which the localization/delocalization transition occurs for all the energies simultaneously. This suggests that these two types of localization are different in nature even though the quantum interference is the key issue in both cases.

It is rather easy to find the disordered system showing the Anderson localization, while there has been no experimental report on the IC-induced localization. Charge (spin) density wave system [4, 5], helical magnets [6], quasi-crystal [7, 8], and two-dimensional electrons under magnetic field (Hofstadter problem) [9] are the representative candidates for it. In the realistic systems, however, there is always some degree of disorder and it is crucial to see the effect of the disorder potential in addition to the IC potential, which we address in this letter.

When one considers the IC potential with one wavevector $\boldsymbol{q}_{\mathrm{IC}}$, which we take along x-axis, the translational symmetry along the two directions y, z perpendicular to $\boldsymbol{q}_{\mathrm{IC}}$ remains intact, and the momenta k_y, k_z are well-defined. Therefore the localization occurs only along x-direction and the wavefunctions are extended along y, z directions. With the disorder, one possible scenario is that the two-dimensional metallic state induced by IC potential is localized by infinitesimal disorder due to the Anderson localization. However, this separation into one and two dimensions breaks down when the disorder is introduced. Namely the scatterings by random potential reduce the spatial anisotropy. Then a keen question is the localization/delocalization in the presence of both IC and disorder potentials. Therefore, the second scenario is that the three-dimensional metal is recovered by the disorder potential. Similar problem arises for the two-dimensional symplectic models which remain metallic for weak disorder strength.

In this paper, we consider a two-dimensional model with spin-orbit interaction. This model belongs to the symplectic universality class and shows a metal-insulator transition at a finite critical strength of disorder without the IC potential, similarly to the three-dimensional case. With the IC potential but without the disorder, there appear localized states along $\boldsymbol{q}_{\mathrm{IC}}$-direction at least for some energy region. The Hamiltonian of this model is given by

$$H = H_0 + V \tag{1}$$

$$H_0 = \sum_{\boldsymbol{r},\boldsymbol{r}'} c^\dagger_{\boldsymbol{r}} t_{\boldsymbol{r}\boldsymbol{r}'} c_{\boldsymbol{r}'}, \tag{2}$$

$$t_{\boldsymbol{r}\boldsymbol{r}'} = \begin{cases} \sqrt{1-S^2}\,t \pm iSt\sigma_y, & \boldsymbol{r} = \boldsymbol{r}' \pm a\boldsymbol{e}_x \\ \sqrt{1-S^2}\,t \mp iSt\sigma_x, & \boldsymbol{r} = \boldsymbol{r}' \pm a\boldsymbol{e}_y \end{cases}, \tag{3}$$

$$V = \sum_{\boldsymbol{r}} c^\dagger_{\boldsymbol{r}} \left[\frac{U}{2} \sin(\boldsymbol{q}_{\mathrm{IC}} \cdot \boldsymbol{r}) + w_{\boldsymbol{r}} \right] c_{\boldsymbol{r}}, \tag{4}$$

where $c^\dagger_{\boldsymbol{r}} = (c^\dagger_{\boldsymbol{r}\uparrow}, c^\dagger_{\boldsymbol{r}\downarrow})$ is the two-component creation operator, while $c_{\boldsymbol{r}}$ is its hermitian conjugate annihilation operator. The term with S in the transfer integral in Eq. (3) represents the spin-orbit interaction, U is the IC potential, and $w_{\boldsymbol{r}}$ is the random disorder potential. The case of $U = 0$ has been studied by Ando [10]. When the Fermi energy is near the band top or bottom, the non-perturbative part H_0 reduces to the Rashba model. In

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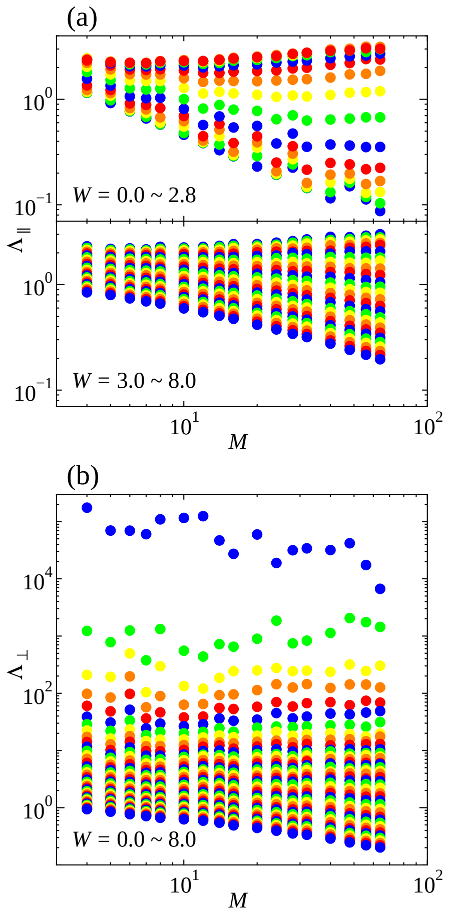

FIG. 1: The renormalized localization (correlation) length, $\Lambda_\alpha(M,W) = \lambda_{\alpha M}(W)/M$, for (a) parallel ($\alpha =\parallel$) and (b) perpendicular ($\alpha =\perp$) direction to $\boldsymbol{q}_{\rm IC}$, at the band center in the system with incommensurate potential of $U = 4.0$ and $\lambda_{\rm IC} = \sqrt{5}$.

the case of $S \ll 1$, the effective mass m^* and the Rashba coupling α are given by $m^* \sim 1/(2ta^2)$ and $\alpha \sim 2Sta$, respectively. We shall take $S = 0.5$ as in Ref. [10] and focus on the energy level around the band center in the rest of this paper. The IC wavevector $\boldsymbol{q}_{\rm IC} = (2\pi/\lambda_{\rm IC})\boldsymbol{e}_x$ is taken along the x-direction with the wavelength $\lambda_{\rm IC}$. The on-site potential $w_{\boldsymbol{r}}$ is randomly distributed in the range $[-W/2, W/2]$. In the following we shall consider the IC potential with $U = 4.0t$ and $\lambda_{\rm IC} = \sqrt{5}a$. The energy unit (hopping parameter) t and the length unit (lattice constant) a are set to be 1 hereafter.

We have calculated the localization length $\lambda_{\alpha M}(W)$ of the above model in the geometry of quasi-one dimensional tube with M-site circumference in terms of the transfer matrix method [11]. We consider the cases in which the direction of tube is parallel ($\alpha =\parallel$) or perpendicular ($\alpha =\perp$) to the IC wavevector $\boldsymbol{q}_{\rm IC}$. The system without IC potential is also analyzed for comparison. Figures 1(a) and 1(b) show the renormalized localization length $\Lambda_\alpha(M,W) = \lambda_{\alpha M}(W)/M$ as a function of the circumference M for several values of the disorder strength W. The length of a tube is taken to be $N = 4\times 10^5$ sites. We have calculated $\Lambda_\alpha(M,W)$ with M = 4, 5, 6, 7, 8, 10, 12, 14, 16, 20, 24, 28, 32, 40, 48, 56, and 64, and W is changed from 0.0 to 8.0 with the interval of 0.2. From the variation of the data for $1/\lambda_{\alpha M}$, we have estimated its error, which is at most a few percent at $\lambda_{\alpha M} < 100$. This means that the error for $\Lambda_\parallel$ in Fig. 1(a) is at most a few percent, while it is comparable to the average for the data $\Lambda_\perp > 2\times 10^1$ in Fig. 1(b), as suggested also by their scattered behavior. We present these data for $\Lambda_\perp > 2\times 10^1$ to show only the systematic tendency. In Fig. 1(b), $\Lambda_\perp$ is monotonously decreasing with increasing W. On the other hand, $\Lambda_\parallel$ is nonmonotonic as shown in Fig. 1(a); in the upper panel of Fig. 1(a), the disorder potential W increases from bottom to the top, while it is reversed in the lower panel. The lowest curve in the upper panel of Fig. 1(a) corresponds to $W = 0$, where only the IC potential is at work and the wavefunction is strongly localized along $\boldsymbol{q}_{\rm IC}$, while it is extended perpendicular to it since k_y is a good quantum number. (The top curve in Fig. 1(b) shows that $\lambda_{\perp M}$ reaches the sample size $N = 4\times 10^5$.)

With finite $W < 2.8$, $\Lambda_\parallel$ shows a nonmonotonous behavior as a function of M; it decreases for $M < M_c(W)$ and turns to increase for $M > M_c(W)$. This means that there appears a crossover length scale $M_c(W)$, which is a decreasing function of W, from localized to extended states along $\boldsymbol{q}_{\rm IC}$. In this range of W and M we have studied, it is clear that the single-parameter scaling does not hold, and it is not clear if $M_c(W)$ diverges as $W \to W_c > 0$ or $W \to 0$. However, it is convincing that the originally localized state along $\boldsymbol{q}_{\rm IC}$-direction turns to be extended with the disorder W. A tentative estimate of $M_c(W)$ from the upper panel of Fig. 1(a) is

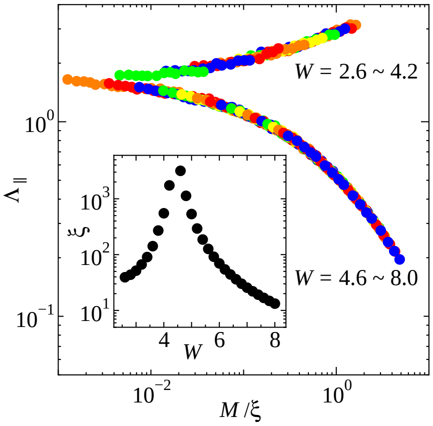

FIG. 2: Renormalized localization (correlation) length, $\Lambda_\parallel(M,W) = \lambda_{\parallel M}(W)/M$, parallel to $\boldsymbol{q}_{\rm IC}$ as a function of $M/\xi(W)$ where $\xi(W)$ is the localization (correlation) length in the thermodynamic limit. (Inset) the localization (correlation) length $\xi(W)$ as a function of W.

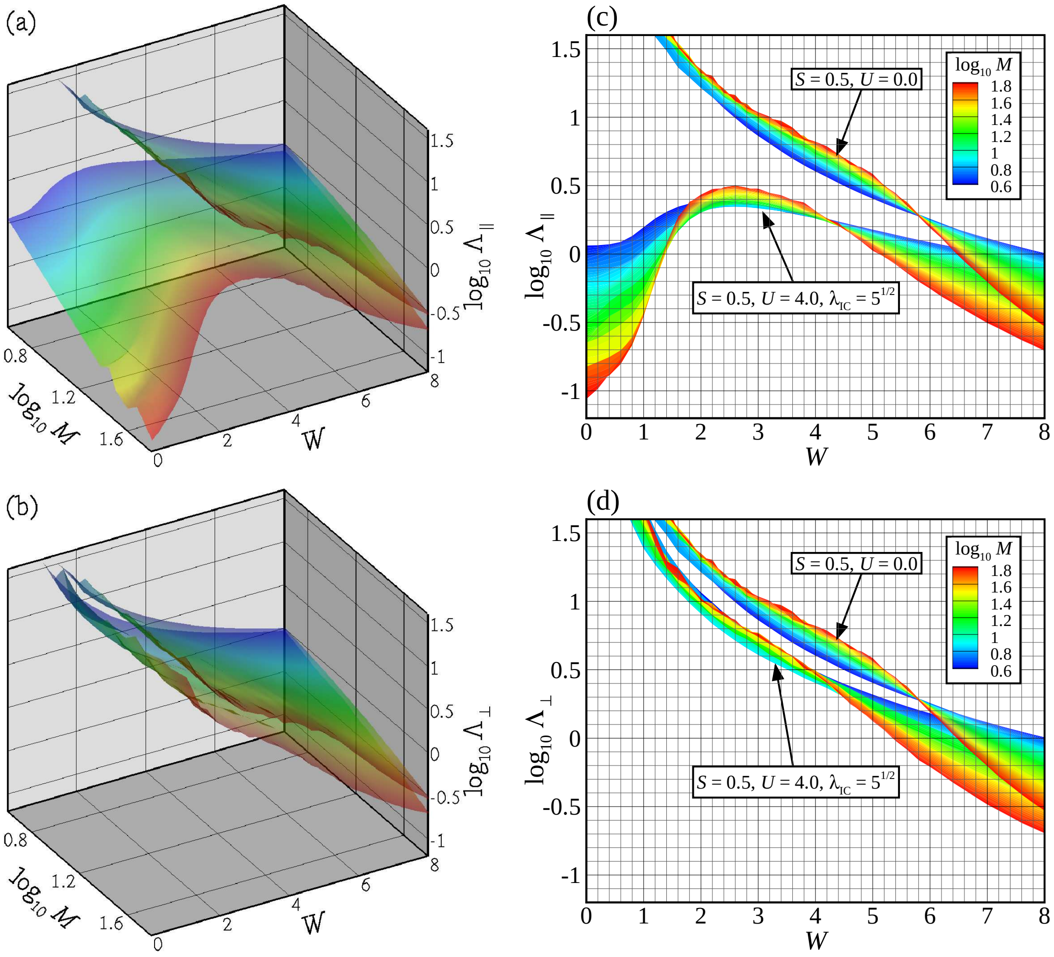

FIG. 3: Birds-eye view of renormalized localization (correlation) length, $\Lambda_{\alpha}(M,W) = \lambda_{\alpha M}(W)/M$, for (a) parallel ($\alpha =\parallel$) and (b) perpendicular ($\alpha =\perp$) direction to $\boldsymbol{q}_{\rm IC}$, at the band center as a function of W and M. In each of (a) and (b),the upper and lower planes represents the cases without and with the IC potential, respectively. The projections of (a) and (b) to the W-Λ plane are shown in (c) and (d), respectively.

$M_c(W = 1.2) \sim 40$ (7-th green curve from the bottom), $M_c(W = 1.6) \sim 20$ (9-th orange curve from the bottom), $M_c(W = 2.0) \sim 10$ (11-th blue curve from the bottom). These values are roughly consistent with the relation $M_c(W) \propto W^{-2}$, which suggests that $M_c(W)$ scales with the elastic mean free path due to the disorder, beyond which the incommensurability is lost and the system behaves as an anisotropic two-dimensional system. For weak disorder, the elastic mean free path $\ell(W)$ is roughly estimated as $\ell(W) \sim 48a(t/W)^2$. The above formula is derived from the estimations of the mean free time τ as $\tau^{-1} \sim \pi\langle w_{\boldsymbol{r}}^2\rangle N_F$, the density of states per unite cell $N_F \sim 1/(2\pi t)$, the averaged disorder strength $\langle w_{\boldsymbol{r}}^2\rangle \sim W^2/12$ for the rectangular distribution, and the Fermi velocity $v_F \sim 2ta$ around the band center. This estimation semi-quantitatively supports the identification, $M_c(W) \sim \ell(W)$, since $\ell(W = 1.2) \sim 33$, $\ell(W = 1.6) \sim 19$ and $\ell(W = 2.0) \sim 12$, for this regime of disorder.

In the lower panel of Fig. 1(a), on the other hand, W increases from the top ($W = 3.0$) to the bottom ($W = 8.0$). At $W = 3.0$, $M_c(W)$ is almost the lattice constant and $\Lambda_{\parallel}$ shows the monotonous behavior as a function of M for $W > 3.0$. This is similar to $\Lambda_{\perp}$ in Fig. 1(b), and is the canonical behavior of the metal-insulator transition. Therefore we show in Fig. 2 its single-parameter scaling analysis [12] from the lower panel of Fig. 1(a). The degeneracy of the data indicating the scaling relation

$$\Lambda_{\parallel} = f_{\parallel}\left(\frac{M}{\xi}\right) \qquad (5)$$

is clearly obtained and the resultant localization/correlation length $\xi(W)$ is plotted in the inset of Fig. 2. (In the upper branch, only the data for $M \geqq 8$ are used.)

The divergence of $\xi(W)$ toward $W_c = 4.3{\pm}0.1$ does not contradict with the relation $\xi(W) \sim |W - W_c|^{-\nu}$ with the known critical exponent $\nu = 2.7 \pm 0.1$, although we did not try the accurate estimate of ν. Therefore we believe that the present metal-insulator transition belongs to the universality class of two-dimensional symplectic one [10, 13, 14].

In order to obtain a global picture, we plot in Figures 3(a) and 3(b) the birds-eye view of the renormalized localization length $\Lambda_\alpha(M, W) = \lambda_{\alpha M}(W)/M$ as a function of the circumference M and the disorder strength W for (a) $\alpha =\parallel$ and (b) $\alpha =\perp$. In Figs. 3(c) and 3(d), we also put the projections of Figs. 3(a) and 3(b) to the W-Λ_α plane, respectively. In each panel, two curved surfaces are shown. The upper (lower) surfaces are for the case without (with) IC potential. It should be noted that the color contour represents the value of M in logarithmic scale, different from the colors in Figs. 1 and 2, in order to make the connection to the projected figures on the right-hand side. From the $\Lambda_\parallel$ with $U = 4.0$ in Figs. 3(a) and 3(c), it is clearly seen that the state is localized, i.e., the red part is lower than the blue one, at both small $W \cong 0$ and large $W > W_c = 4.3 \pm 0.1$. The degeneracy occurs at W_c indicates the metal-insulator transition as analyzed in Figs. 1 and 2, while one can not see any degeneracy for smaller W. Therefore, the reversal of the M-dependence around $W \cong 1.5$ is attributed to the crossover at $M_c(W)$ as discussed above. The behavior of $\Lambda_\perp$ in Figs. 3(b) and 3(d), on the other hand, is similar to the case of $U = 0$. Note that the critical W_c is common for both $\Lambda_\parallel$ and $\Lambda_\perp$, which is reduced from $W_c = 5.8 \pm 0.1$ to $W_c = 4.3 \pm 0.1$ by the IC potential $U = 4.0$.

Now we discuss the relevance of these results to the experimental observation of the localization due to IC potential. Except the one-dimensionally confined systems such as quantum wire, the electronic wavefunctions are extended in the perpendicular directions to the IC wavevector. This is almost always the case as in charge (spin) density wave, and helical magnets. In this case, we expect that the elastic scattering by impurities washes out the IC potential in both two and three dimensions beyond the length scale of the elastic mean free path $\ell(W)$. First let us ask the following question: " Can one observe the temperature dependence of the resistivities characteristic to the IC-induced localization ? " To answer to this question, one should remember that the temperature dependence of the resistivity is translated into that of the inelastic mean free path $L_{\rm in}(T)$, which is replaced by the sample size L. The quantum correction due to the interference occurs for the length scale $L > \ell(W)$. Namely, $\ell(W)$ is the shortest length scale for the localization problem, and the Boltzmann transport theory applies for $L < \ell(W)$. Therefore, if the crossover length scale $M_c(W)$ is identical to $\ell(W)$, as suggested by the analysis above, there is no chance to observe the IC-induced localization from the temperature dependence. Most probably this is the reason why there are no experimental observation of the IC-induced localization, i.e., it is very fragile against the disorder and is replaced by the usual Anderson localization. However, the incommensurability gives a strong anisotropy of the metallic conduction between parallel and perpendicular directions to the wavevector $\boldsymbol{q}_{\rm IC}$ within the Boltzmann transport regime, which is the remnant of the IC-induced localization. Therefore, for example, one should look for the dramatic change of the Resistivity anisotropy associated with the commensurate-incommensurate transition.

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